



S/N 10/028643

PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al. Examiner: Long Pham  
Serial No.: 10/028643 Group Art Unit: 2814  
Filed: December 20, 2001 Docket: 1303.030US1  
Title: LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO<sub>3</sub>  
GATE DIELECTRICS

**INFORMATION DISCLOSURE STATEMENT**

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In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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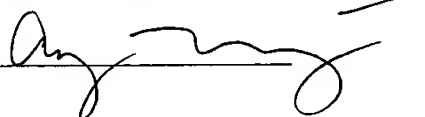
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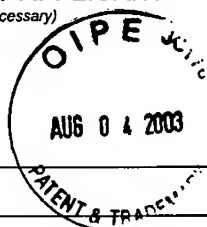


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Application Number	10/028643
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First Named Inventor	Ahn, Kie
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Examiner Name	Pham, Long

Sheet 1 of 6

Attorney Docket No: 1303.030US1

**US PATENT DOCUMENTS**

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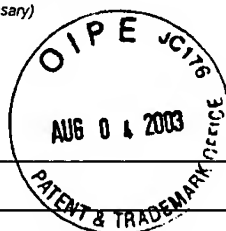
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Sheet 2 of 6

Attorney Docket No: 1303.030US1

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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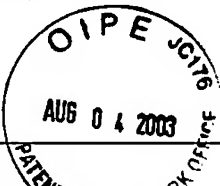
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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		<b>Application Number</b>	10/028643
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		<b>Group Art Unit</b>	2814
		<b>Examiner Name</b>	Pham, Long
Sheet 3 of 6		Attorney Docket No: 1303.030US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		GUSEV, E P., et al., "Ultrathin High-K Dielectrics Grown by Atomic Layer Deposition: A Comparative Study of ZrO <sub>2</sub> , HfO <sub>2</sub> , Y <sub>2</sub> O <sub>3</sub> and Al <sub>2</sub> O <sub>3</sub> ", <u>Electrochemical Society Proceedings Volume 2001-9</u> , (2001),pp. 189-195	
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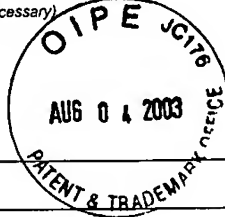
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Examiner Name	Pham, Long

Sheet 4 of 6

Attorney Docket No: 1303.030US1

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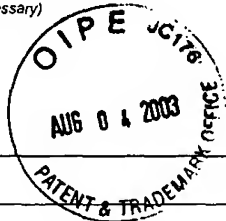
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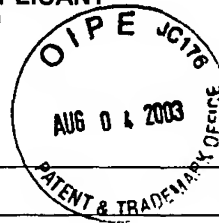
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EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)

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